



# FDMB2307NZ

## Dual Common Drain N-Channel PowerTrench<sup>®</sup> MOSFET 20 V, 9.7 A, 16.5 mΩ

### Features

- Max  $r_{S1S2(on)}$  = 16.5 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 8$  A
- Max  $r_{S1S2(on)}$  = 18 mΩ at  $V_{GS} = 4.2$  V,  $I_D = 7.4$  A
- Max  $r_{S1S2(on)}$  = 21 mΩ at  $V_{GS} = 3.1$  V,  $I_D = 7$  A
- Max  $r_{S1S2(on)}$  = 24 mΩ at  $V_{GS} = 2.5$  V,  $I_D = 6.7$  A
- Low Profile - 0.8 mm maximum - in the new package MicroFET 2x3 mm
- HBM ESD protection level > 2 kV (Note 3)
- RoHS Compliant

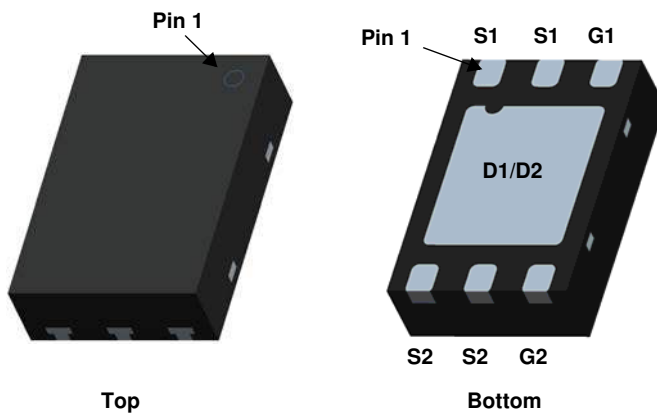


### General Description

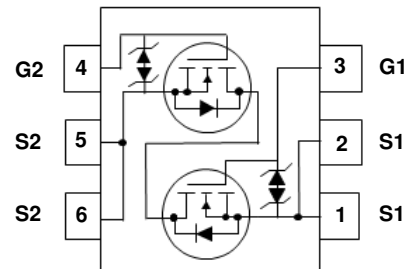
This device is designed specifically as a single package solution for Li-Ion battery pack protection circuit and other ultra-portable applications. It features two common drain N-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench<sup>®</sup> process with state of the art MicroFET Leadframe, the FDMB2307NZ minimizes both PCB space and  $r_{S1S2(on)}$ .

### Application

- Li-Ion Battery Pack



MLP 2x3



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{S1S2}$	Source1 to Source2 Voltage	20	V
$V_{GS}$	Gate to Source Voltage (Note 4)	$\pm 12$	V
$I_{S1S2}$	Source1 to Source2 Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	9.7	A
	-Pulsed	40	
$P_D$	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.2	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b)	0.8	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(Dual Operation) (Note 1a)	57	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(Dual Operation) (Note 1b)	161	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
307	FDMB2307NZ	MLP 2x3	7"	8 mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$I_{S1S2}$	Zero Gate Voltage Source1 to Source2 Current	$V_{S1S2} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = 12\text{ V}, V_{S1S2} = 0\text{ V}$			10	$\mu\text{A}$

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = 250\ \mu\text{A}$	0.6	1	1.5	V
$r_{S1S2(on)}$	Static Source1 to Source2 On Resistance	$V_{GS} = 4.5\text{ V}, I_{S1S2} = 8\text{ A}$	10.5	13.5	16.5	m $\Omega$
		$V_{GS} = 4.2\text{ V}, I_{S1S2} = 7.4\text{ A}$	11	14	18	
		$V_{GS} = 3.1\text{ V}, I_{S1S2} = 7\text{ A}$	11.5	16	21	
		$V_{GS} = 2.5\text{ V}, I_{S1S2} = 6.7\text{ A}$	12	18	24	
		$V_{GS} = 4.5\text{ V}, I_{S1S2} = 8\text{ A}, T_J = 125^\circ\text{C}$	11	20	29	
$g_{FS}$	Forward Transconductance	$V_{S1S2} = 5\text{ V}, I_{S1S2} = 8\text{ A}$		41		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{S1S2} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1760	2640	pF
$C_{oss}$	Output Capacitance			229	345	pF
$C_{rss}$	Reverse Transfer Capacitance			211	320	pF
$R_g$	Gate Resistance (Note 5)		0.1	2.6	8	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{S1S2} = 10\text{ V}, I_{S1S2} = 8\text{ A}, V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		12	22	ns
$t_r$	Rise Time			19	34	ns
$t_{d(off)}$	Turn-Off Delay Time			32	51	ns
$t_f$	Fall Time			9.5	17	ns
$Q_g$	Total Gate Charge		$V_{G1S1} = 0\text{ V to } 5\text{ V}$		20	28
$Q_g$	Total Gate Charge	$V_{G1S1} = 0\text{ V to } 4.5\text{ V}$		18	25	nC
$Q_{gs}$	Gate1 to Source1 Charge	$V_{S1S2} = 10\text{ V}, I_{S1S2} = 8\text{ A}, V_{G2S2} = 0\text{ V}$		2.8		nC
$Q_{gd}$	Gate1 to Source2 "Miller" Charge			5.3		nC

### Source1- Source2 Diode Characteristics

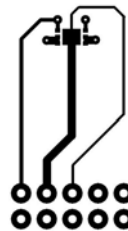
$I_{fss}$	Maximum Continuous Source1-Source2 Diode Forward Current			8	A	
$V_{fss}$	Source1 to Source2 Diode Forward Voltage	$V_{G1S1} = 0\text{ V}, V_{G2S2} = 4.5\text{ V}, I_{fss} = 8\text{ A}$ (Note 2)		0.8	1.2	V

#### NOTES:

- $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



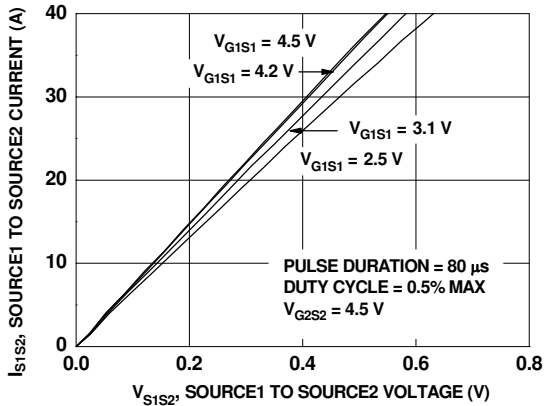
a. 57 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



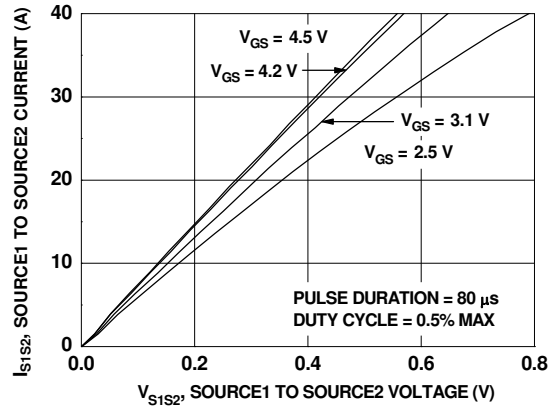
b. 161 °C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.
- As an N-ch device, the negative  $V_{gs}$  rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
- $R_g$  is measured on 100% of the die at wafer level.

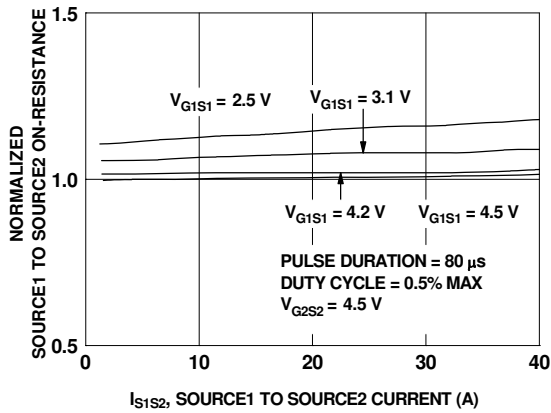
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



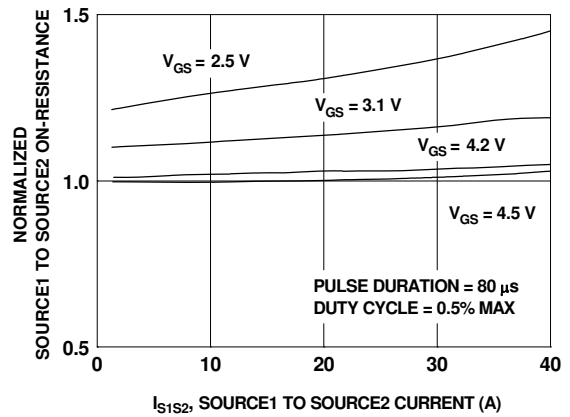
**Figure 1. On-Region Characteristics**



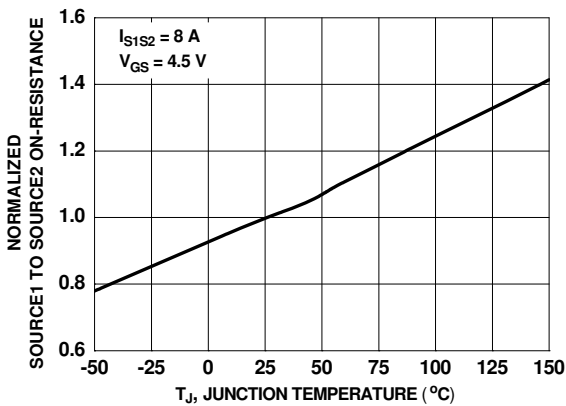
**Figure 2. On-Region Characteristics**



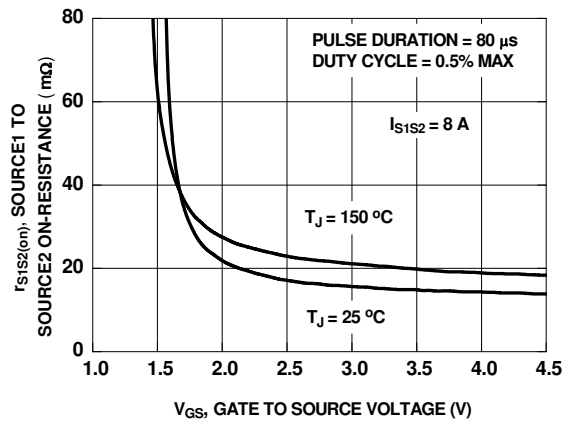
**Figure 3. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage**



**Figure 4. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage**

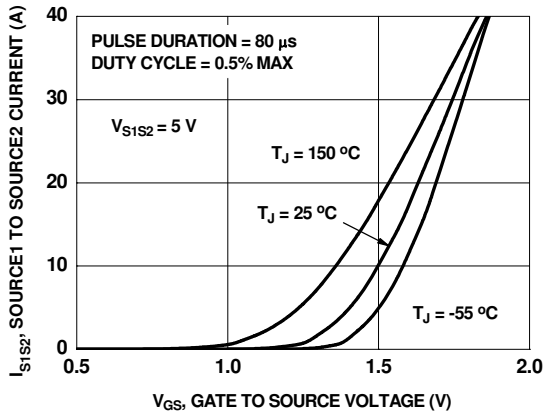


**Figure 5. Normalized On Resistance vs Junction Temperature**

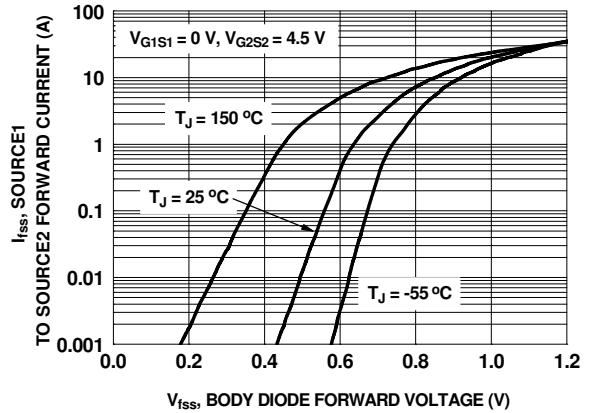


**Figure 6. On Resistance vs Gate to Source Voltage**

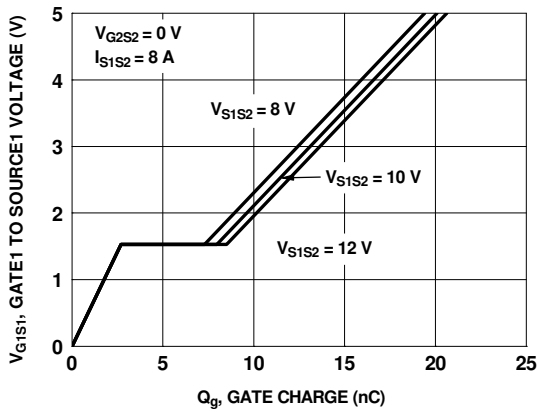
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



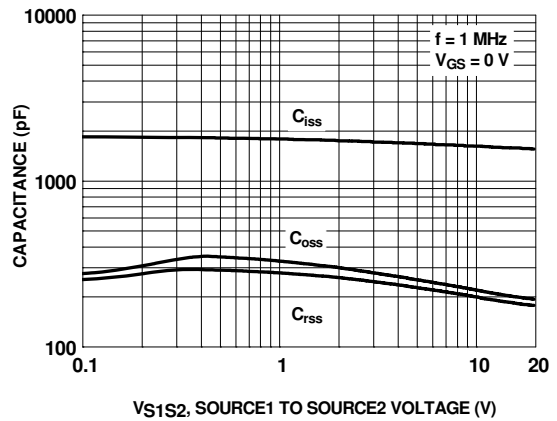
**Figure 7. Transfer Characteristics**



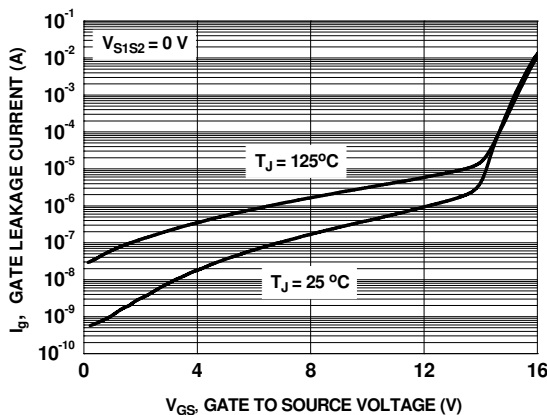
**Figure 8. Source1 to Source2 Diode Forward Voltage vs Source Current**



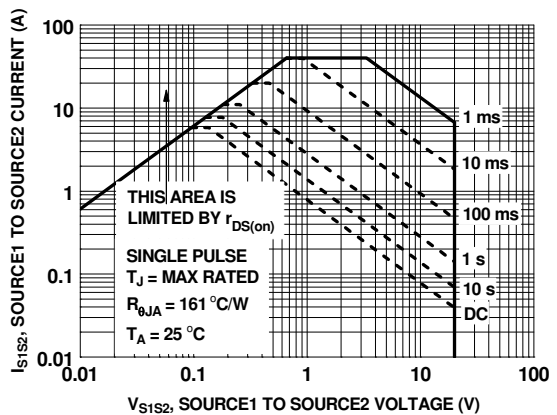
**Figure 9. Gate Charge Characteristics**



**Figure 10. Capacitance vs Source1 to Source2 Voltage**

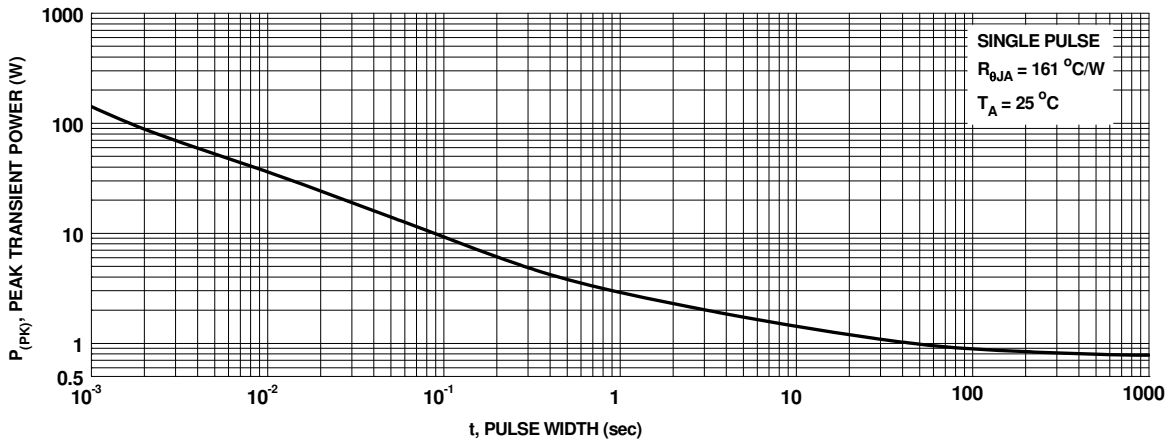


**Figure 11. Gate Leakage Current vs Gate to Source Voltage**

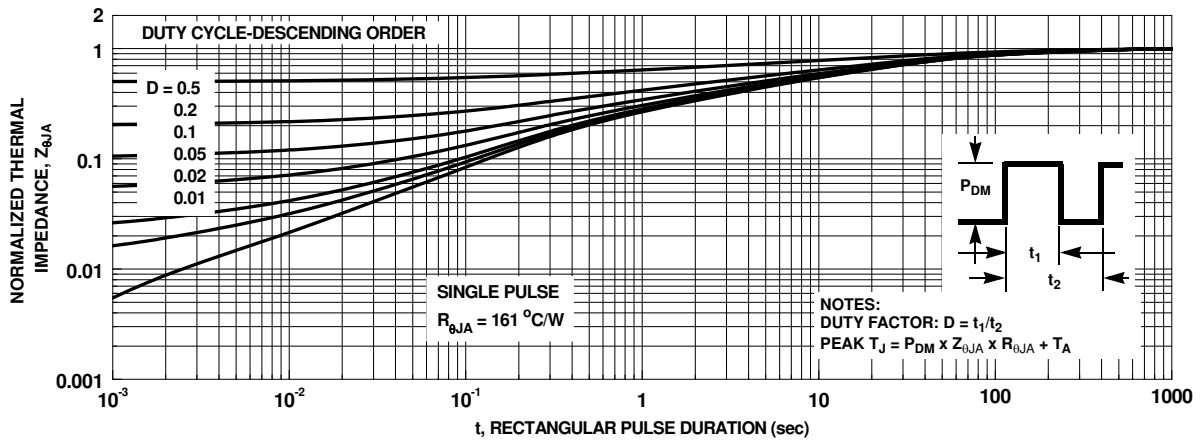


**Figure 12. Forward Bias Safe Operating Area**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

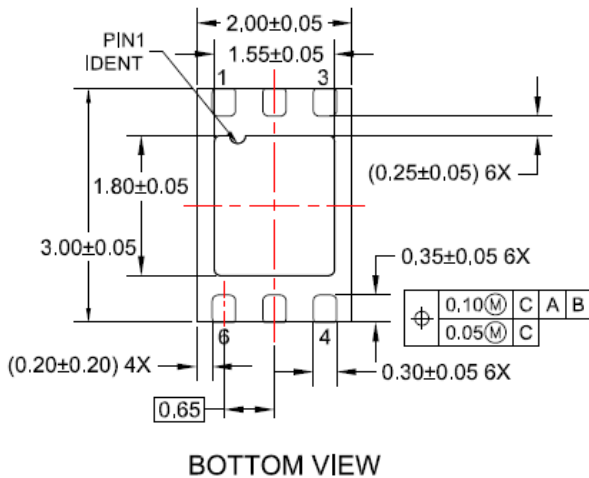
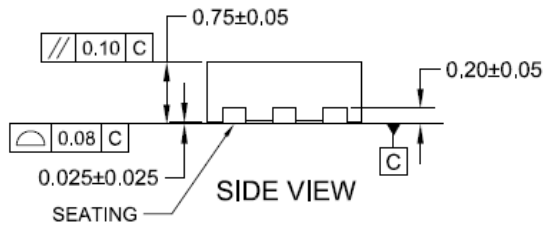
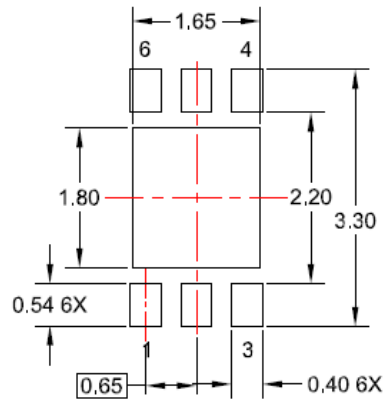
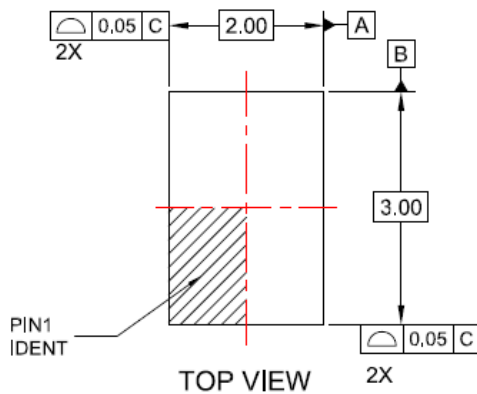


**Figure 13. Single Pulse Maximum Power Dissipation**



**Figure 14. Junction-to-Ambient Transient Thermal Response Curve**

## Dimensional Outline and Pad Layout



### NOTES:

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- B. DRAWING FILENAME: MKT-MLP06Qrev3.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
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